

- (10) (((finfet fin adj2 (fet mosfet mos transistor))
 (9296036) contact plug interconnect\$4 connect\$4 via
 (43676) (contact plug interconnect\$4 connect\$4 via) near6 (bl bitline bit adj line readin
 (23) ((contact plug interconnect\$4 connect\$4 via) near6 (bl bitline bit adj line readin
 (4) (((contact plug interconnect\$4 connect\$4 via) near6 (bl bitline bit adj line readin
 (894236) gate
 (526070) nm nanometer nano adj meter angstrom
 (24) (((finfet fin adj2 (fet mosfet mos transistor))
 (22) (((finfet fin adj2 (fet mosfet mos transistor))
 (17) (((finfet fin adj2 (fet mosfet mos transistor))
 (2) "20040099835"
 (1) "20040099835" and (nm nanometer nano adj meter angstrom)
 (569848) nm nanometer nano adj meter angstrom ang
 (1) "20040099835" and (nm nanometer nano adj meter angstrom ang)
 (164)((finfet fin adj2 (fet mosfet mos transistor))
 (1) "20030102518" and (nm nanometer nano adj meter angstrom ang)
 (4) 10/083330
 (4) 10/083330 and (nm nanometer nano adj meter angstrom ang)
 (0) "20030102518" and ((wordline "WL" ((word digit control adj gate) adj line) twor
 (2) "20030102518"

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